

Title (en)

SEMICONDUCTOR DIODE, ELECTRONIC COMPONENT, VOLTAGE SOURCE INVERTER AND CONTROL METHOD

Title (de)

HALBLEITERDIODE, ELEKTRONISCHES BAUTEIL, SPANNUNGSZWISCHENKREISUMRICHTER UND STEUERVERFAHREN

Title (fr)

DIODE A SEMI-CONDUCTEUR, COMPOSANT ELECTRONIQUE, CONVERTISSEUR DE CIRCUIT DE TENSION INTERMEDIAIRE ET PROCEDE DE COMMANDE

Publication

**EP 1597771 A2 20051123 (DE)**

Application

**EP 04712009 A 20040218**

Priority

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Abstract (en)

[origin: WO2004077573A2] The invention relates to a semiconductor diode, an electronic component and to a voltage source inverter. According to the invention, the semiconductor diode having at least one pn-transition can be switched between a first state and a second state. In comparison to the first state, the second state has a greater on-state resistance and a smaller accumulated charge, and the pn-transition is capable of blocking both in the first state as well as in the second state with at least one predetermined blocking ability. An MOS-controlled diode is hereby obtained in which the transition from the on-state to the blocking state is simplified and is thus not critical with regard to the temporal sequence of the control pulses.

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IPC 8 full level

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Citation (search report)

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